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Application Number	10/730755
Filing Date	12-8-03
First Named Inventor	Andy Horch
Art Unit	2813
Examiner Name	
Attorney Docket Number	C016-D-1

Sheet	1	of	2
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U. S. PATENT DOCUMENTS

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**Examiner
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Cin. a. 22

Date
Considered

20 June 2005

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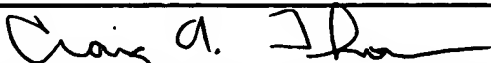
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		Examiner Name	
Sheet 2	of 2	Attorney Docket Number	C016-D-1

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CAT		K. DeMeyer, S. Kubicek and H. van Meer, Raised Source/Drains with Disposable Spacers for sub 100 nm CMOS Technologies, Extended Abstracts of International Workshop on Junction Technology 2001.	
CAT		Mark Rodder and D. Yeakley, Raised Source/Drain MOSFET with Dual Sidewall Spacers, IEEE Electron Device Letters, Vol. 12, No. 3, March 1991	
CAT		Yang-Kyu Choi, Daewon Ha, Tsu-Jae King and Chenming Hu, Nanoscale Ultrathin PMOSFETs with Raised Selective Germanium Source/Drain, IEEE Electron Device Letters, Vol. 22, No. 9, September 2001.	
CAT		N. Lindert, Y. K. Choi, L. Chang, E. Anderson, W. C. Lee, T. J. King, J. Bokor, and C. Hu, Quasi-Planar FinFETs with Selectively Grown Germanium Raised Source/Drain, 2001 IEEE International SOI Conference, 10/2001	
CAT		T. Ohguro, H. Naruse, H. Sugaya, S. Nakamura, E. Morifuji, H. Kimijima, T. Yoshitomi, T. Morimoto, H.S. Momose, Y. Katsumata, and H. Iwai, High Performance RF Characteristics of Raised Gate/Source/Drain CMOS with Co Salicide, 1998 Symposium on VLSI Technology Digest of Technical Papers	
CAT		Hsiang-Jen Huang, Kun-Ming Chen, Tiao-Yuan Huang, Tien-Sheng Chao, Guo-Wei Huang, Chao-Hsin Chien, and Chun-Yen Chang, Improved Low Temperature Characteristics of P-Channel MOSFETs with Si1-xGe _x Raised Source and Drain, IEEE Transactions on Electron Devices, Vol. 48, No. 8, August 2001	
CAT		Plummer, James, D. and Scharf, Brad W., Insulated-Gate Planar Thyristors, I-Structure and Basic Operation, pp. 380-386	
CAT		Stanley Wolf Ph.D. and Richard N. Tauber Ph.D., Silicon Processing for the VLSI Era, Vol. 1, 1986, page 285-286	

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